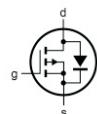
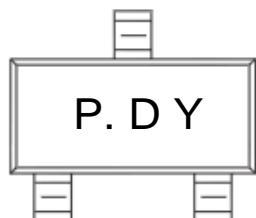


P-Channel Enhancement Mode MOSFET

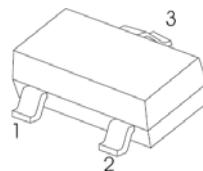
■ Features

- V_{DS} (V) = -50V
- I_D = -0.13 A
- $R_{DS(ON)} \leq 10 \Omega$ ($V_{GS} = -5V$)

MARKING



SOT - 23



1. GATE
2. SOURCE
3. DRAIN

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	-50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current * – Continuous – Pulsed	I_D	-130	mA
		-520	
Total Power Dissipation *	P_d	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch;

■ Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	Bv_{DSS}	$V_{GS} = 0V, I_D = -250\mu\text{A}$	-50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -50V, V_{GS} = 0V, T_J = 25^\circ\text{C}$			-15	μA
		$V_{DS} = -50V, V_{GS} = 0V, T_J = 125^\circ\text{C}$			-60	μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 10	nA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -1\text{mA}$	-0.8		-2.0	V
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	$V_{GS} = -5V, I_D = -100\text{mA}$			10	Ω
Forward Transconductance	g_{FS}	$V_{DS} = -25V, I_D = -0.1\text{A}$	0.05			S
Input Capacitance	C_{iss}	$V_{DS} = -25V, V_{GS} = 0V, f = 1.0\text{MHz}$			45	pF
Output Capacitance	C_{oss}				25	pF
Reverse Transfer Capacitance	C_{rss}				12	pF
Turn-On Delay Time	$t_{D(\text{ON})}$	$V_{DD} = -30V, I_D = -0.27\text{A}, R_{GEN} = 50\Omega, V_{GS} = -10V$		10		ns
Turn-Off Delay Time	$t_{D(\text{OFF})}$			18		ns

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)